

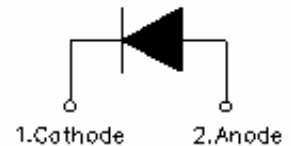
## MBR20100 SCHOTTKY RECTIFIER

### Applications:

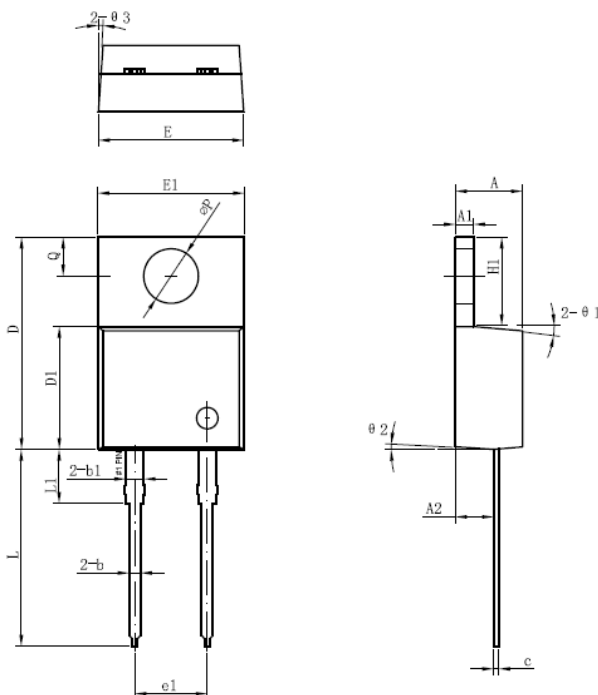
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

### Features:

- 150 °C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



### Mechanical Dimensions (In mm)

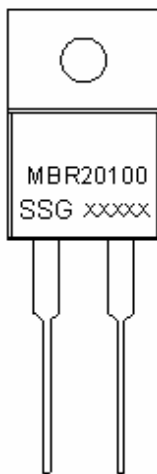


Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.64	14.94	15.24
D1	8.55	8.07	8.85
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1		5.08	
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1		3.80	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		5°	
Θ2		4°	
Θ3		4°	

### TO-220AC



**Marking Diagram:**



Where XXXXX is YYWWL

MBR = Device Type  
20 = Forward Current (20A)  
100 = Reverse Voltage (100V)  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
MBR20100	TO-220AC(Pb-Free)	50pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	100	
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=125\text{ }^\circ\text{C}$ , rectangular wave form	20	A
Max. Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse	280	A



**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	$V_{F1}$	@ 20 A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.88	V
	$V_{F2}$	@ 20 A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.74	V
Max. Reverse Current (per leg) *	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_C = 25\text{ }^\circ\text{C}$	1.0	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_C = 125\text{ }^\circ\text{C}$	6	mA
Max. Junction Capacitance (per leg)	$C_T$	@ $V_R = 5\text{ V}$ , $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$	400	pF
Typical Series Inductance (per leg)	$L_S$	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ $\mu\text{s}$

\* Pulse Width < 300 $\mu\text{s}$ , Duty Cycle <2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	$T_J$	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	$^\circ\text{C}$
Max. Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	3.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	1.6	g
Case Style	TO-220AC			

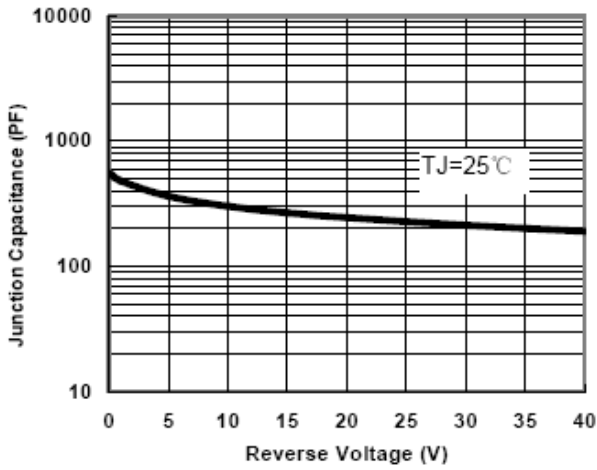


Fig.1-Typical Junction Capacitance

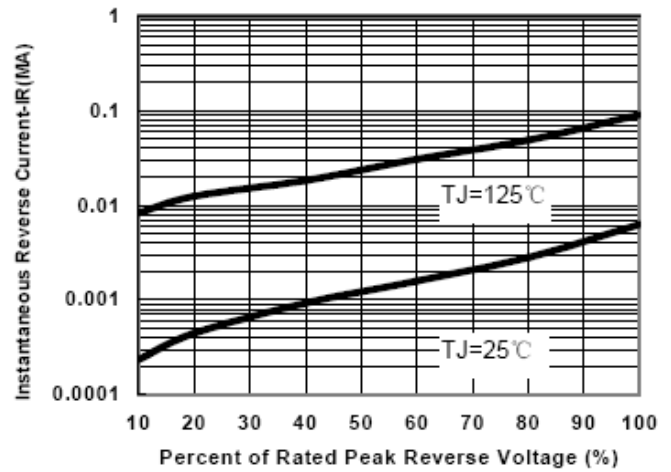


Fig.2-Typical Reverse Characteristics

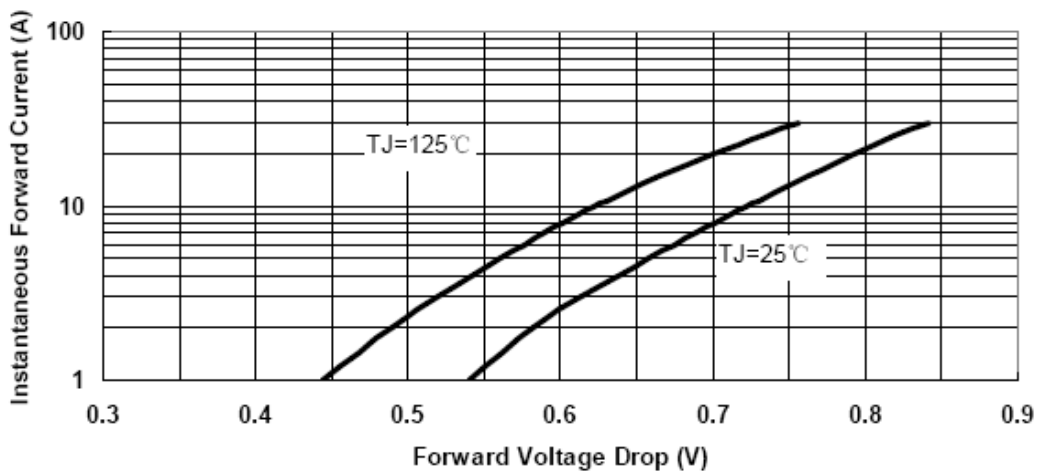


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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